

--ABSTRACT OF THE DISCLOSURE

A semiconductor memory device may include: (1) a word line drive circuit, having a drive transistor disposed between a positive power supply and a word line, (2) a circuit for turning the drive transistor OFF after an output of the word line drive circuit reaches a high level, and (3) a word-line-voltage increasing circuit for increasing a voltage of the word line after the drive transistor turns OFF. The word-line-voltage increasing circuit includes a coupling capacitor, one end of which is connected to the word line, and a capacitor drive circuit, an output end of which is connected to the other end of the coupling capacitor. The capacitor drive circuit switches its output from a low level to a high level at a timing when the drive transistor is OFF.--